

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N5232A

NPN SILICON TRANSISTOR

JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5232A type is a NPN Silicon Planar Epitaxial Transistors designed for low noise amplifier applications.

MAXIMUM RATINGS (T_A = 25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	70	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	I _C	100	mA
Power Dissipation	P _D	625	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	0.2	°C/mW

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} = 50V			30	nA
I _{CBO}	V _{CB} = 50V, T _A = 100°C			10	μA
I _{CES}	V _{CB} = 50V			30	nA
I _{EBO}	V _{EB} = 5.0V			50	nA
BV _{CB0}	I _C = 10μA	70			V
BV _{CEO}	I _C = 10mA	50			V
BV _{EBO}	I _C = 10μA	5.0			V
V _{CE(SAT)}	I _C = 10mA, I _B = 1.0mA			0.125	V
V _{BE(SAT)}	I _C = 10mA, I _B = 1.0mA			0.780	V
V _{BE(ON)}	V _{CE} = 10V, I _C = 2.0mA	0.500		0.900	V
h _{FE}	V _{CE} = 5.0V, I _C = 2.0mA	250		500	
h _{fe}	V _{CE} = 5.0V, I _C = 2.0mA, f = 1.0kHz	250		750	
C _{ob}	V _{CB} = 10V, I _E = 0, f = 1.0MHz			4.0	pF
NF	V _{CE} = 5.0V, I _C = 100μA, R _g = 5kΩ f = 1kHz, BW = 15.7kHz		1.9	5.0	dB